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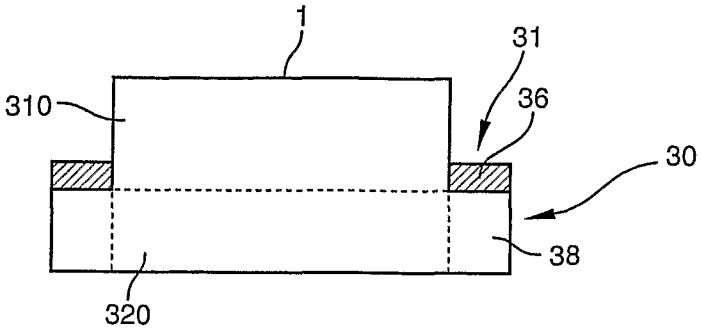
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[Continued on next page]

(54) Title: METHOD OF PRODUCTION OF A FILM



(57) Abstract: The invention relates to a method of producing a film intended for applications in electronics, optics or optronics starting from an initial wafer, which includes a step of implanting atomic species through one of the faces of the wafer, which method comprises the following stages: (a) formation of a step of determined height around the periphery of the wafer, the mean thickness of the wafer at the step being less than the mean thickness of the rest of the wafer; (b) protection of said step against the implantation of atomic species; and (c) implantation of atomic species through that face of the wafer having said step, so as to form an implanted zone at a determined implant depth, said film being determined, on one side, by the implanted face of the wafer and, on the other side, by the implanted zone. The invention also relates to a wafer obtained by said method.

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